



## **40V N-Channel Enhancement Mode MOSFET**

Voltage

40 V

Current

61 A

#### **Features**

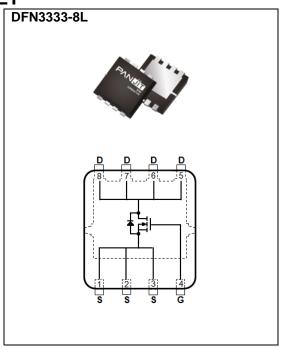
- RDS(ON), VGS@10V, ID@15A<6.3m $\Omega$
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@7V, I<sub>D</sub>@10A<7.7mΩ
- Excellent FOM
- Standard Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	40	V	
Gate-Source Voltage		V <sub>GS</sub>	±20	V	
Continuous Drain Current(Note 3)	Tc=25°C		61		
	T <sub>C</sub> =100°C	l <sub>D</sub>	43	Α	
Pulsed Drain Current(Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	244		
Power Dissipation	T <sub>C</sub> =25°C	_	42	10/	
	Tc=100°C	Po	21	W	
Continuous Drain Current(Note 4)	T <sub>A</sub> =25°C		15	۸	
	T <sub>A</sub> =70°C	I <sub>D</sub>	12.4	A	
Power Dissipation	T <sub>A</sub> =25°C	D-	2.5	147	
	T <sub>A</sub> =70°C	Po	1.8	W	
Single Pulse Avalanche Energy(Note 5)		Eas	85	mJ	
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~175	°C	
Thermal Resistance <sup>(Note 4)</sup>	Junction to Case	R <sub>0JC</sub>	3.6	°C/W	
	Junction to Ambient	$R_{\theta JA}$	60	C/VV	





### **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static			_				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	-	-	- V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =50uA	2	2.8	3.5	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	-	5	6.3	mΩ	
		V <sub>GS</sub> =7V, I <sub>D</sub> =10A	-	5.9	7.7		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA	
Dynamic <sup>(Note 6)</sup>		•	•				
Total Gate Charge	$Q_g$	V <sub>DS</sub> =32V, I <sub>D</sub> =15A,	-	23	-	nC	
Gate-Source Charge	$Q_{gs}$		-	5	-		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V <sup>(Note 2,3)</sup>	-	6	-		
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	1283	-	pF	
Output Capacitance	Coss		-	252	-		
Reverse Transfer Capacitance	Crss	f=1MHZ	-	45	-		
Gate resistance	Rg	f=1MHZ	-	0.8	-	Ω	
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DS</sub> =32V, I <sub>D</sub> =15A,	-	14	-	ns	
Turn-On Rise Time	tr		-	3	-		
Turn-Off Delay Time	td <sub>(off)</sub>	V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	24	-		
Turn-Off Fall Time	tf	(11016-2,3)	-	5	-		
Drain-Source Diode		•	•				
Diode Forward Current	Is	│ ┐ Tc=25°C	-	-	61	_	
Pulsed Diode Forward Current	I <sub>SM</sub>	1c=25 C	-	-	244	Α	
Diode Forward Voltage	V <sub>SD</sub>	Is=20A, V <sub>G</sub> s=0V	-	0.85	1.3	V	
Reverse Recovery Time	Trr	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	24	-	ns	
Reverse Recovery Charge	Qrr	dl <sub>S</sub> /dt=100A/us	-	11	-	nC	

#### NOTES:

- 1. Pulse width<100us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an  $R_{\theta JC}=3.6^{\circ}C/W$ .
- 4.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH,  $I_{AS}$ =18A,  $V_{DD}$ =30V,  $V_{GS}$ =10V, Starting  $T_{J}$ =25°C.
- 6. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

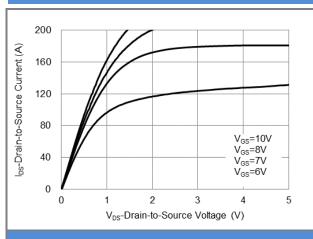


Fig.1 On-Region Characteristics

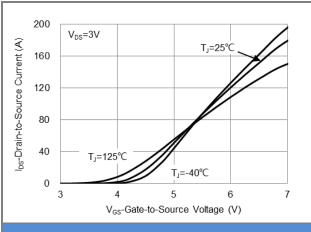


Fig.2 Transfer Characteristics

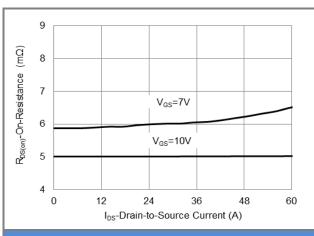


Fig.3 On-Resistance vs. Drain Current

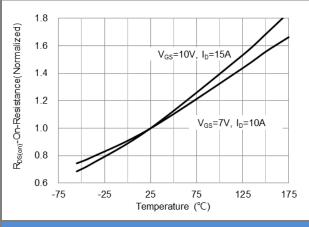


Fig.4 On-Resistance vs. Junction temperature

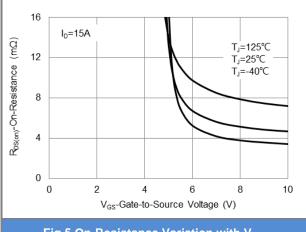


Fig.5 On-Resistance Variation with V<sub>GS</sub>

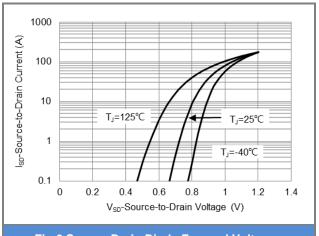


Fig.6 Source-Drain Diode Forward Voltage





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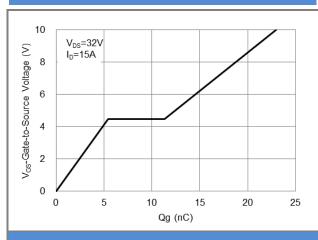


Fig.7 Gate-Charge Characteristics

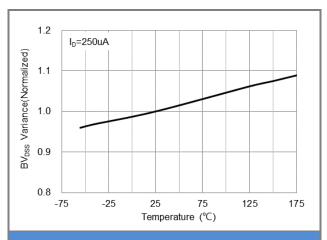


Fig.8 Breakdown Voltage Variation vs. Temperature

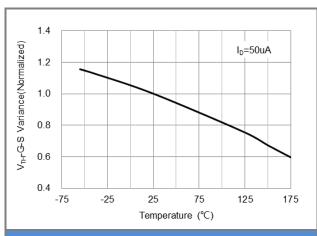


Fig.9 Threshold Voltage Variation with Temperature

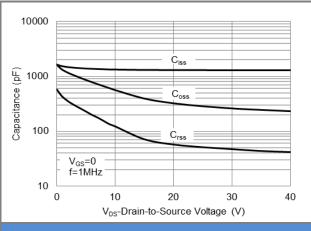


Fig.10 Capacitance vs. Drain-Source Voltage

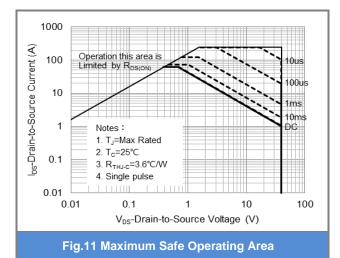
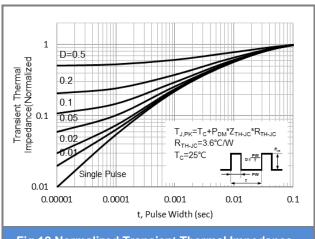


Fig.12 Normalized Transient Thermal Impedance



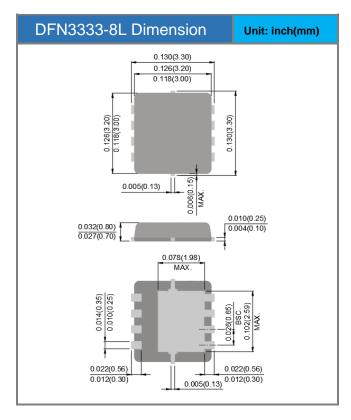


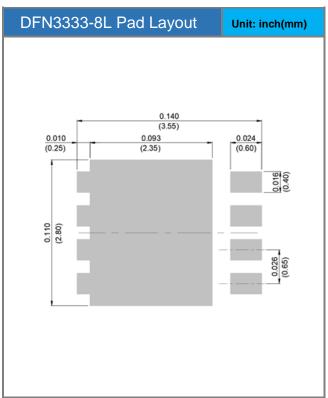


### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking	
PJQ4546VP-AU	DFN3333-8L	5K pcs / 13" reel	546V	

## **Packaging Information & Mounting Pad Layout**









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